

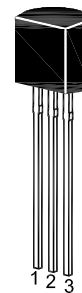
2N5400 / 2N5401

PNP Silicon Epitaxial Planar Transistors

for general purpose, high voltage amplifier applications.

As complementary types the NPN transistors 2N5550 and 2N5551 are recommended.

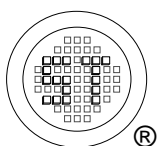
On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|---------------------------|------------|---------------|------------------|
| Collector Base Voltage | $-V_{CBO}$ | 130 160 | V |
| Collector Emitter Voltage | $-V_{CEO}$ | 120 150 | V |
| Emitter Base Voltage | $-V_{EBO}$ | 5 | V |
| Collector Current | $-I_C$ | 600 | mA |
| Power Dissipation | P_{tot} | 625 | mW |
| Junction Temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | - 55 to + 150 | $^\circ\text{C}$ |



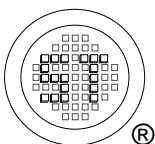
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2N5400 / 2N5401

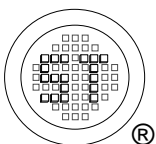
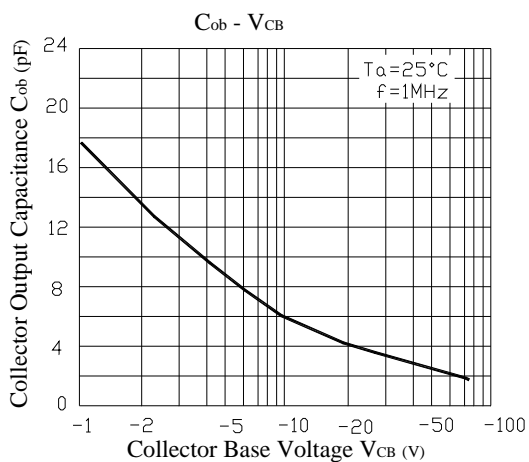
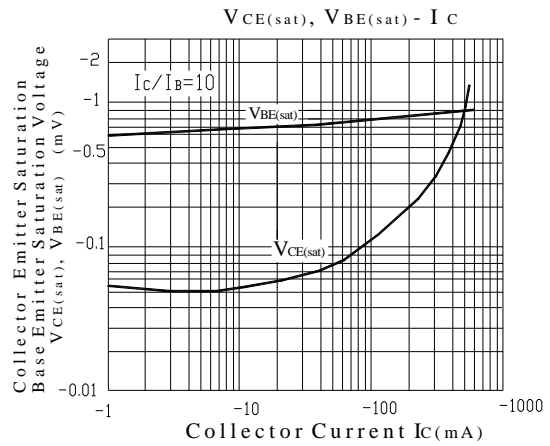
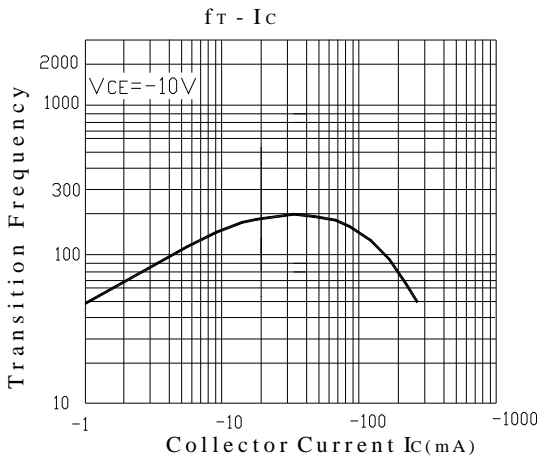
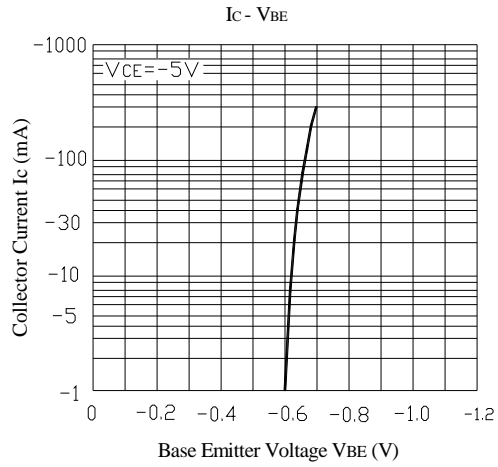
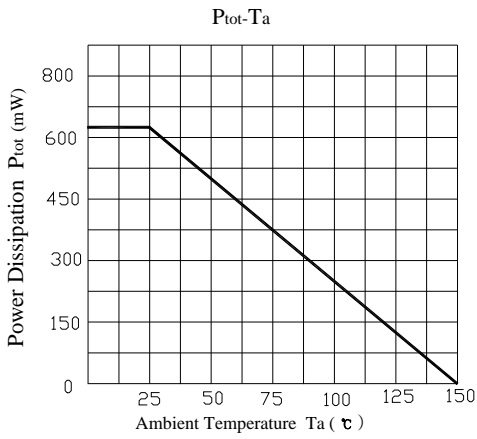
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter | | Symbol | Min. | Max. | Unit |
|---|--------|----------------|------|------|------|
| DC Current Gain at $-V_{CE} = 5\text{ V}$, $-I_C = 1\text{ mA}$ at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$ at $-V_{CE} = 5\text{ V}$, $-I_C = 50\text{ mA}$ | 2N5400 | h_{FE} | 30 | - | - |
| | 2N5401 | h_{FE} | 50 | - | - |
| | 2N5400 | h_{FE} | 40 | 180 | - |
| | 2N5401 | h_{FE} | 60 | 240 | - |
| | 2N5400 | h_{FE} | 40 | - | - |
| | 2N5401 | h_{FE} | 50 | - | - |
| Collector Base Cutoff Current at $-V_{CB} = 100\text{ V}$ at $-V_{CB} = 120\text{ V}$ | 2N5400 | $-I_{CBO}$ | - | 100 | nA |
| | 2N5401 | | - | 50 | |
| Emitter Base Cutoff Current at $-V_{EB} = 3\text{ V}$ | | $-I_{EBO}$ | - | 50 | nA |
| Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$ | 2N5400 | $-V_{(BR)CBO}$ | 130 | - | V |
| | 2N5401 | | 160 | - | |
| Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$ | 2N5400 | $-V_{(BR)CEO}$ | 120 | - | V |
| | 2N5401 | | 150 | - | |
| Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$ | | $-V_{(BR)EBO}$ | 5 | - | V |
| Collector Emitter Saturation Voltage at $-I_C = 10\text{ mA}$, $-I_B = 1\text{ mA}$ at $-I_C = 50\text{ mA}$, $-I_B = 5\text{ mA}$ | | $-V_{CE(sat)}$ | - | 0.2 | V |
| | | | - | 0.5 | |
| Base Emitter Saturation Voltage at $-I_C = 10\text{ mA}$, $-I_B = 1\text{ mA}$ at $-I_C = 50\text{ mA}$, $-I_B = 5\text{ mA}$ | | $-V_{BE(sat)}$ | - | 1 | V |
| | | | - | 1 | |
| Gain Bandwidth Product at $-V_{CE} = 10\text{ V}$, $-I_C = 10\text{ mA}$, $f = 100\text{ MHz}$ | | f_T | 100 | 400 | MHz |
| Collector Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$ | | C_{ob} | - | 6 | pF |



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